

SiO₂ enclosing of TiO₂ nanoparticles from a two step DBD process

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Titanium dioxide nano particles are used commonly in various applications due to their high catalytic activity. Many of these applications require subsequent treatments after the deposition of the TiO_2 particles. Some of these include thermal processing at high temperatures, e.g. roof tiles. During such procedures the nano particles transform from the catalytical highly active anatas structure to the substantially less active rutil structure. This structural change has been found to be significantly retarded when coating the TiO_2 nano particles with a closed film of SiO₂. During the thermal treatment, these films break open, revealing the underlying TiO_2 . Thus, the film thickness has to be appropriate for the designated treatment subsequent to the nano particle deposition.

In this study, we present an approach of SiO₂ film deposition out of silan gas. For technical implementations, test gas containing about 1.5% silan in 98.5% nitrogen is preferred over pure silan, since much less precautions are needed. Closed films produced by dielectric barrier discharges in such mixtures of gases consist of mainly nonstoichiometric silicon nitride. The conversion of this silicon nitride layer to silicon dioxide is shown to be largely possible by subsequent plasma treatment in different atmospheres such as pure O_2 , as well as in environmental air. All studies have been carried out in an ultra high vacuum apparatus, while the plasma treatments have been carried out at atmospheric pressure. During the investigations we employed metastable induced electron spectroscopy, ultraviolet photoelectron spectroscopy, X-ray photoelectron spectroscopy and atomic force microscopy.

2. Experimental

For probing the surface density of states (SDOS) we applied MIES and UPS using a hemispherical analyzer (VSW HA100) combined with a source for metastable helium atoms (mainly $He^{23}S_1$) and ultraviolet photons (HeI). Additional information for chemical analysis was obtained by XPS utilizing a commercial non-monochromatic X-ray source (Specs RQ20/38C) using Al K α at a photon energy of 1486.6 eV. Fit curves were gained using OriginPro 7G with the Peak Fitting Module. A Veeco Dimension 3100 SPM is employed for tapping mode AFM with silicon cantilevers (NSC15 with Al backside coating from Micromasch).

Plasma treatments have been carried out employing alternating high voltage pulses with a peak voltage of 11 kV, a pulse duration of 0.6 µs and a pulse repetition rate of 10 kHz. The used process gases were O_2 (Linde Gas, 99.995%), N_2 (Linde Gas, >99.8%), atmospheric air and a silane gas mixture (Linde Gas) consisting of 1.5% SiH₄ (99.999%) and 98.5% N₂ (99.9996%).

3. Sample preparation







4. SiH₄,N₂ plasma treatment (1st step)



Stoichiometry:	
С	5.9%
N	20.1%
Ti	6.0%
Si	46.5%
0	20.6%

Carbon reduction

• Ti₂O₃ defects at particle surfaces • Non-stoichiometric Si₃N cover layer











suspensed in ethanol (d₅₀ ~ 21 nm, >99.5%)

5a. O₂ plasma treatment (2nd step)



- Complete removal of carbon
- Severe reduction of nitrogen
- Healing of interfacial Ti₂O₃ defects
- Transformation of cover layer into substoichiometric SiO₂



5. Discussion

5b. Air plasma treatment (2nd step)



- Further removal of carbon
- Severe reduction of nitrogen
- Healing of interfacial Ti₂O₃ defects
- Transformation of cover layer into substoichiometric SiO₂



See also: S. Dahle, L. Wegewitz, A. Weber, W. Maus-Friedrichs, International Conference on Plasma Surface Engineering (2012)

6. Literature

- F. J. Trompeter, PHD thesis at the RWTH Aachen, 2001.
- B. M. Penetrante, M. C. Hsiao, J. N. Bardsley, B. T. Merritt, G. W. Vogtlin, A. Kuthi, [2] C. P. Burkhart, J. R. Bayless, Plasma Sources Sci. Technol. 6 (1997) 251–259.
- N. L. Aleksandrov, E. M. Bazelyan, I. V. Kochetov, N. A. Dyatko, [3] J. Phys. D: Appl. Phys. **30** (1997) 1616–1624.
- L. G. Piper, G. E. Caledonia, J. P. Kennealy, J. Chem. Phys. 74 (1981) 2888–2895. [4]

Dividing the plasma-based deposition of SiO₂ into the two steps of silicon deposition and transformation towards silicon oxide led to...

- 1. The deposition of non-stoichiometric Si₃N during the first step and
- 2. The transformation into a nearly stoichiometric SiO_2 film during the second step,
- 3. Which fully encloses the initial clusters of TiO_2 particles.

63.9%

0

- 4. Thus, the deposition process employing SiH_4 as precursor gets simplified very much.
- 5. Additionally, an implicit cleaning and passivation of the nanoparticles' surfaces from all adsorbats took place.
- The dependence of the deposition and the transformation steps is currently Outlook: being investigated in more detail.

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